

AMENDMENTS TO THE SPECIFICATION

Please amend the specification as follows:

At page 7, line 8, please insert the following new paragraph:

FIGS. 7(A)-(F) illustrate cross-sectional views, plan-views, and dark-field plan views of exemplary aspects of the device 600, according to the present invention.

At page 12, line 8, please inset the following new paragraphs:

Figures 7(A) and 7(B) exemplarily illustrate cross-sections of polycrystalline metal showing the orientation of a low index crystal plane (e.g., oriented crystal planes of crystal grains), according to exemplary aspects of the present invention.

Figures 7(C) and 7(D) exemplarily illustrate plan-views of polycrystalline metal showing the orientation of crystal grains (e.g., oriented crystal faces including closed packed planes), according to exemplary aspects of the present invention.

Figures 7(E) exemplarily illustrates a dark-field plan-view TEM micrograph of a Pt film deposited on a p-GaN substrate at room temperature, according to exemplary aspects of the present invention. The average grain size is approximately 10 nm.

Figure 7(F) exemplarily illustrates a dark-field plan-view TEM micrograph of a Pt film deposited on p-GaN substrate at 573K, according to exemplary aspects of the present invention. The average grain size is greater than 100 nm.